

*“Gas ratio effects on the Si etch rate and profile uniformity in an inductively coupled Ar/CF<sub>4</sub> plasma”*. Zhao S-X, Gao F, Wang Y-N, Bogaerts A, Plasma sources science and technology **2**, 015017 (2013). <http://doi.org/10.1088/0963-0252/22/1/015017>